

PSMN1R2-30YLD

N-channel 30 V, 1.2 m Ω , 250 A logic level MOSFET in LFPAK56 using NextPowerS3 Technology

21 December 2018

Product data sheet

1. General description

250 A logic level gate drive N-channel enhancement mode MOSFET in LFPAK56 package. NextPowerS3 portfolio utilising Nexperia's unique "SchottkyPlus" technology delivers high efficiency, low spiking performance usually associated with MOSFETs with an integrated Schottky or Schottky-like diode but without problematic high leakage current. NextPowerS3 is particularly suited to high efficiency applications at high switching frequencies.

2. Features and benefits

- 250 A capability
- Ultra low Q_G, Q_{GD} and Q_{OSS} for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery; s-factor > 1
- · Low spiking and ringing for low EMI designs
- Unique "SchottkyPlus" technology; Schottky-like performance with < 1 µA leakage at 25 °C
- Optimised for 4.5 V gate drive
- Low parasitic inductance and resistance
- High reliability clip bonded and solder die attach Power SO8 package; no glue, no wire bonds, qualified to 175 °C
- Wave solderable; exposed leads for optimal visual solder inspection

3. Applications

- On-board DC-to-DC solutions for server and telecommunications
- · Secondary-side synchronous rectification in telecommunication applications
- Voltage regulator modules (VRM)
- Point-of-Load (POL) modules
- Power delivery for V-core, ASIC, DDR, GPU, VGA and system components
- · Brushed and brushless motor control
- Power OR-ing

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C		-	-	30	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	250	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	194	W
Tj	junction temperature			-55	-	175	°C
Static characteristics							
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 10		-	1.2	1.6	mΩ



Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
		V_{GS} = 10 V; I_{D} = 25 A; T_{j} = 25 °C; Fig. 10		-	0.96	1.24	mΩ	
Dynamic chara	cteristics			•				
Q_{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$		-	9.1	-	nC	
Q _{G(tot)}	total gate charge	Fig. 12; Fig. 13		-	32	-	nC	
Source-drain d	Source-drain diode							
S	softness factor	I_S = 25 A; dI_S/dt = -100 A/ μ s; V_{GS} = 0 V; V_{DS} = 15 V; $Fig.~16$		-	0.95	-		

^{[1] 250}A continuous current has been successfully demonstrated during application test. Practically, the current will be limited by PCB, thermal design and operating temperature.

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	D
2	S	source	<u> </u>	
3	S	source		G—(F)
4	G	gate		mbb076 S
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PSMN1R2-30YLD	LFPAK56; Power-SO8	Plastic single-ended surface-mounted package (LFPAK56; Power-SO8); 4 leads	SOT669		

7. Marking

Table 4. Marking codes

Type number	Marking code
PSMN1R2-30YLD	1D230L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T _j ≤ 175 °C	-	30	V
V_{DGR}	drain-gate voltage	25 °C ≤ T_j ≤ 175 °C; R_{GS} = 20 kΩ	-	30	V
V_{GS}	gate-source voltage		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>	-	194	W

Symbol	Parameter	Conditions		Min	Max	Unit
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	250	Α
		V _{GS} = 10 V; T _{mb} = 100 °C; <u>Fig. 2</u>		-	209	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 °C$; Fig. 3		-	1181	Α
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
V _{ESD}	electrostatic discharge voltage	НВМ		1500	-	V
Source-drai	n diode		'	'	•	
I _S	source current	T _{mb} = 25 °C		-	162	Α
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C		-	1181	Α
Avalanche r	uggedness				•	
E _{DS(AL)S}	non-repetitive drain- source avalanche energy	I_D = 25 A; $V_{sup} \le 30$ V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; t_p = 1.97 ms	[2]	-	961	mJ

^{[1] 250}A continuous current has been successfully demonstrated during application test. Practically, the current will be limited by PCB, thermal design and operating temperature.



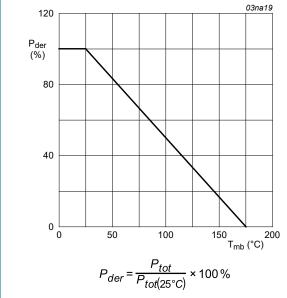
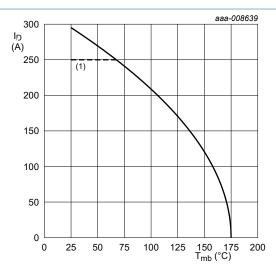


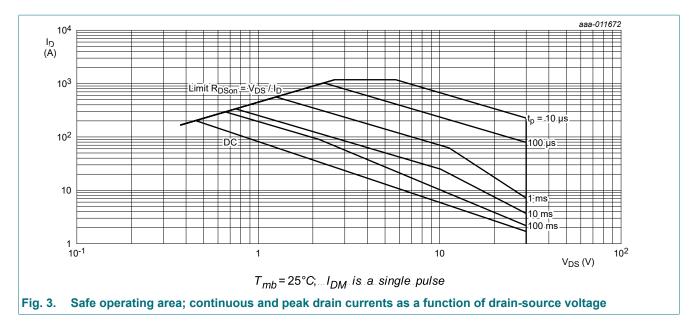
Fig. 1. Normalized total power dissipation as a function of mounting base temperature



(1) 250A Continuous current has been successfully demonstrate during application tests. Practically the current will be limited by PCB, thermal design and operation temperature.

$$V_{GS} \ge 10V$$

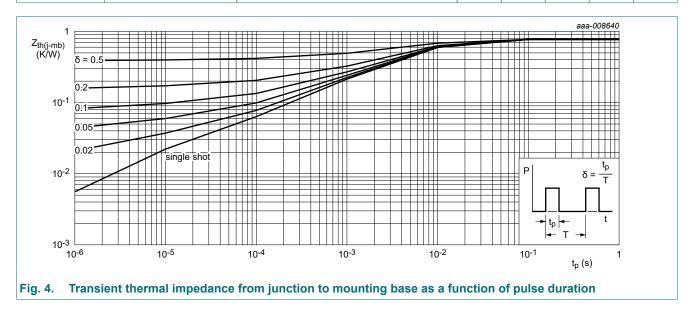
Fig. 2. Continuous drain current as a function of mounting base temperature



9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 4	-	0.69	0.77	K/W
R _{th(j-a)} thermal resistance from junction to ambient	Fig. 5	-	50	-	K/W	
	Fig. 6	-	125	-	K/W	



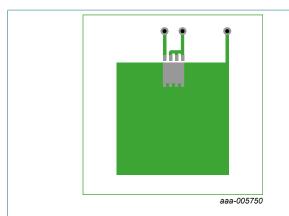


Fig. 5. PCB layout for thermal resistance junction to ambient 1" square pad; FR4 Board; 2oz copper

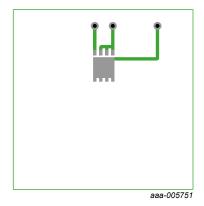


Fig. 6. PCB layout for thermal resistance junction to ambient minimum footprint;FR4 board; 2oz copper

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	cteristics				'	
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
	breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 2 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.2	1.7	2.2	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T _j ≤ 150 °C	-	-4.7	-	mV/K
I _{DSS}	drain leakage current	V _{DS} = 24 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{DS} = 24 V; V _{GS} = 0 V; T _j = 125 °C	-	1.9	-	μΑ
I _{GSS}	gate leakage current	V _{GS} = 16 V; V _{DS} = 0 V; T _j = 25 °C	-	-	100	nA
		$V_{GS} = -16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 10	-	1.2	1.6	mΩ
		V _{GS} = 4.5 V; I _D = 25 A; T _j = 150 °C; Fig. 10; Fig. 11	-	-	2.64	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 10	-	0.96	1.24	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 150 °C; Fig. 10; Fig. 11	-	-	2.05	mΩ
R _G	gate resistance	f = 1 MHz	-	1.15	-	Ω
Dynamic cha	aracteristics					
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 15 V; V _{GS} = 10 V; Fig. 12; Fig. 13	-	68	-	nC
		I _D = 25 A; V _{DS} = 15 V; V _{GS} = 4.5 V; Fig. 12; Fig. 13	-	32	-	nC
		I _D = 0 A; V _{DS} = 0 V; V _{GS} = 10 V	-	62	-	nC
Q _{GS}	gate-source charge $I_D = 25 \text{ A}$; $V_{DS} = 15 \text{ V}$; $V_{GS} = 4.5 \text{ V}$;		-	9.9	-	nC
Q _{GS(th)}	pre-threshold gate- source charge	Fig. 12; Fig. 13	-	6.4	-	nC

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q _{GS(th-pl)}	post-threshold gate- source charge			-	3.5	-	nC
Q_{GD}	gate-drain charge			-	9.1	-	nC
V _{GS(pl)}	gate-source plateau voltage	I _D = 25 A; V _{DS} = 15 V; <u>Fig. 12</u> ; <u>Fig. 13</u>		-	2.5	-	V
C _{iss}	input capacitance	V _{DS} = 15 V; V _{GS} = 0 V; f = 1 MHz;		-	4616	-	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 14</u>		-	2079	-	pF
C _{rss}	reverse transfer capacitance	-		-	293	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 0.6 \Omega; V_{GS} = 4.5 \text{ V};$		-	25.3	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$		-	31	-	ns
t _{d(off)}	turn-off delay time			-	38.7	-	ns
t _f	fall time			-	25.5	-	ns
Q _{oss}	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$		-	47.4	-	nC
Source-drai	n diode						
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 15$		-	0.78	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	43.2	-	ns
Q _r	recovered charge	V _{DS} = 15 V; <u>Fig. 16</u>	[1]	-	43	-	nC
t _a	reverse recovery rise time			-	22.2	-	ns
t _b	reverse recovery fall time			-	21	-	ns
S	softness factor	1		-	0.95	-	
		1					

[1] includes capacitive recovery

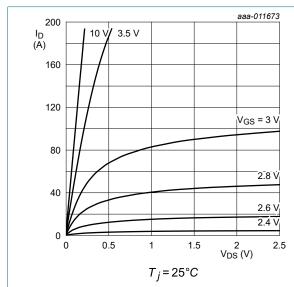


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

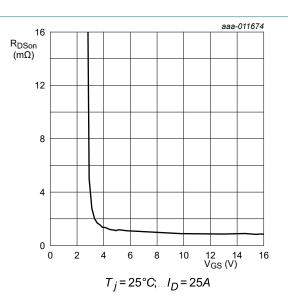
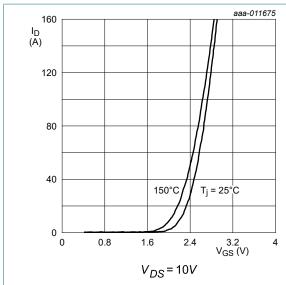


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

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Transfer characteristics; drain current as a function of gate-source voltage; typical values

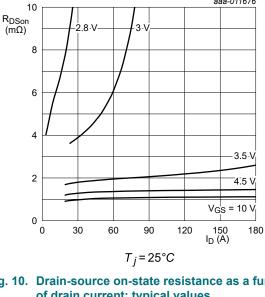


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

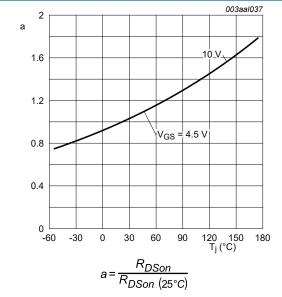


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

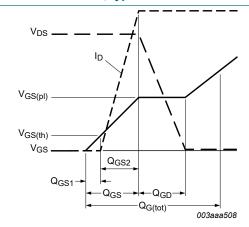


Fig. 12. Gate charge waveform definitions

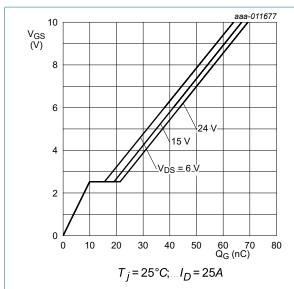


Fig. 13. Gate-source voltage as a function of gate charge; typical values

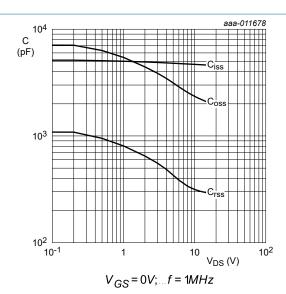


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

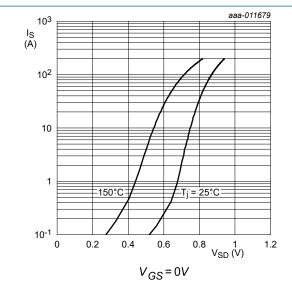


Fig. 15. Source current as a function of source-drain voltage; typical values

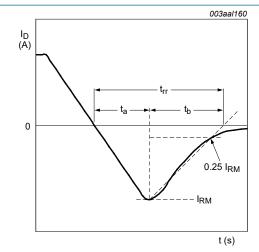
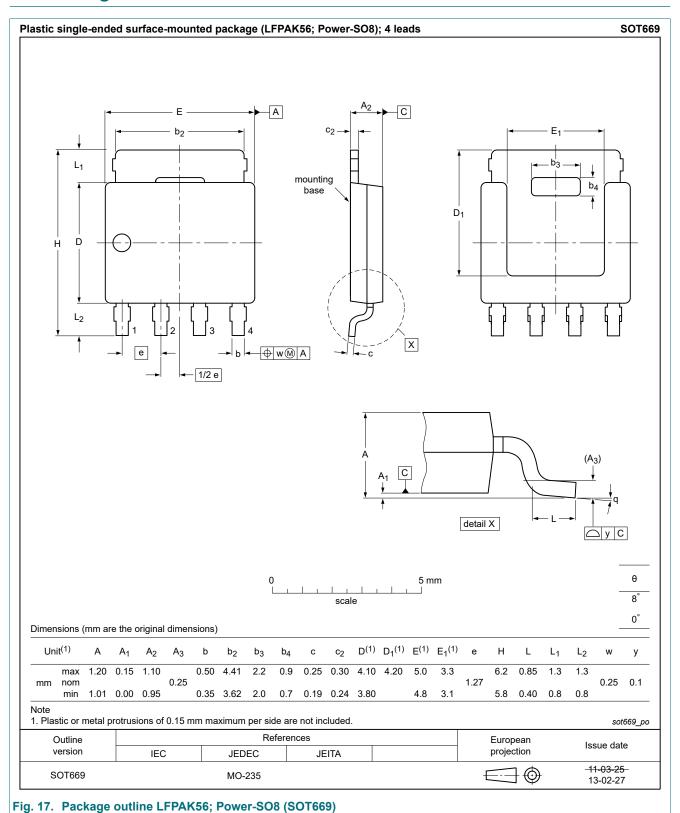


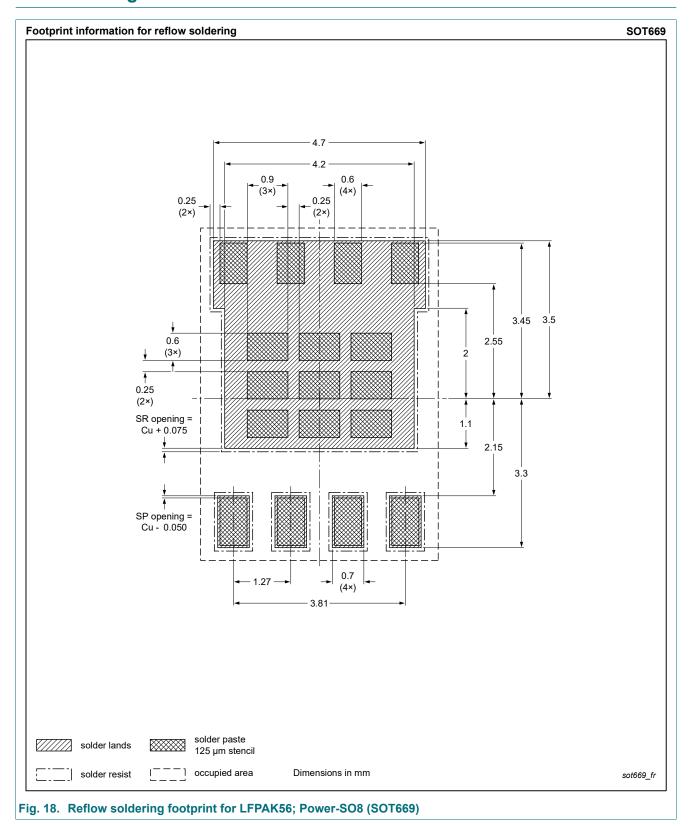
Fig. 16. Reverse recovery timing definition

11. Package outline



PSMN1R2-30YLD

12. Soldering



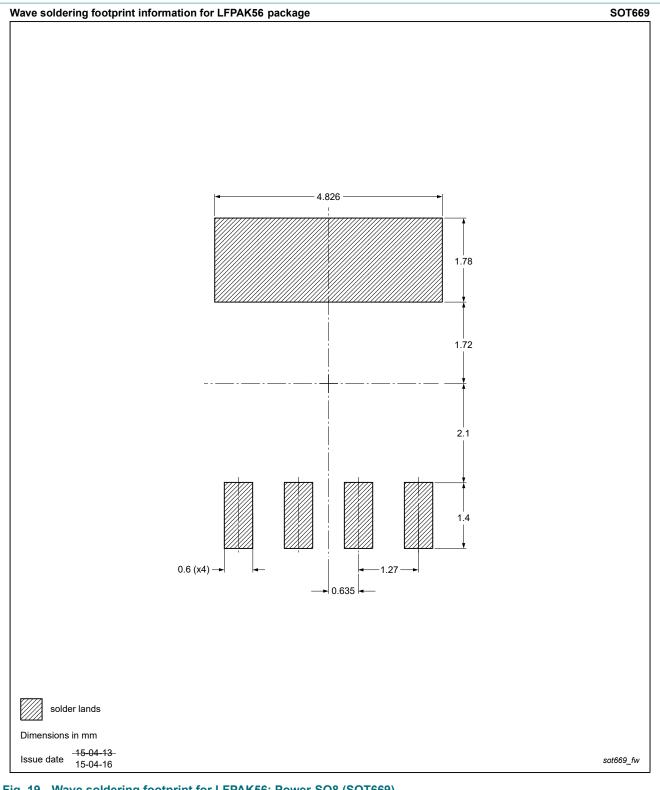


Fig. 19. Wave soldering footprint for LFPAK56; Power-SO8 (SOT669)

13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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